

# NUP4212UPMU

## ESD Protection Diode Array, Quad, Ultra-Low Capacitance

The four-line surge protection array is designed to protect voltage-sensitive components that require ultra-low capacitance from ESD and transient voltage events. This device features a common anode design which can protect up to four independent high speed data lines and 1 or 2 separate 15 V surge protection lines in a single six-lead UDFN low profile package.

Excellent clamping capability, low capacitance, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as a USB 2.0 high speed.

This device can be configured as a dual port USB device.

### Features

- Low Capacitance Data Lines (0.7 pF Typical)
- Protects up to Four Data Lines Plus a V<sub>CC</sub> Pin
- UDFN Package, 1.6 x 1.6 mm
- Low Profile of 0.50 mm for Ultra Slim Design
- V<sub>1</sub>, V<sub>2</sub> Pin = 15 V Protection
- D<sub>1</sub>, D<sub>2</sub>, D<sub>3</sub>, and D<sub>4</sub> Pins = 5.2 V Minimum Protection
- ESD Rating: IEC61000-4-2: Level 4  
– Contact (14 kV)
- This is a Pb-Free Device

### Typical Applications

- USB 2.0 High-Speed Interface
- Cell Phones
- MP3 Players
- SIM Card Protection

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
T <sub>J</sub>	Operating Junction Temperature Range	-40 to 125	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>L</sub>	Lead Solder Temperature – Maximum (10 seconds)	260	°C
ESD	IEC 61000-4-2 Contact	14000	V

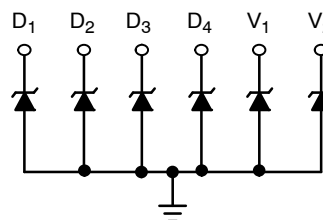
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

See Application Note AND8308/D for further description of survivability specs.



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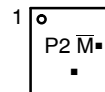
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### MARKING DIAGRAM



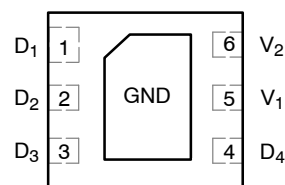
UDFN6 1.6 X 1.6  
MU SUFFIX  
CASE 517AP



- P2 = Specific Device Code
- M̄ = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

### PIN CONNECTIONS



### ORDERING INFORMATION

Device	Package	Shipping†
NUP4212UPMUTAG	UDFN6 (Pb-Free)	3000/Tape & Reel

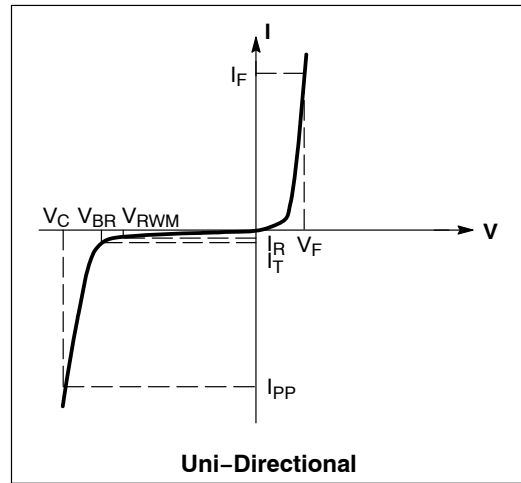
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$
$P_{pk}$	Peak Power Dissipation
C	Max. Capacitance @ $V_R = 0$ and $f = 1.0$ MHz



\*See Application Note AND8308/D for detailed explanations of datasheet parameters.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Reverse Working Voltage ( $D_1, D_2, D_3,$ and $D_4$ )	(Note 1)	$V_{RWM1}$	-	-	4.0	V
Reverse Working Voltage ( $V_1$ and $V_2$ )	(Note 1)	$V_{RWM2}$	-	-	12	V
Breakdown Voltage ( $D_1, D_2, D_3,$ and $D_4$ )	$I_T = 1$ mA, (Note 2)	$V_{BR}$	5.2	5.5	-	V
Breakdown Voltage ( $V_1, V_2$ )	$I_T = 5$ mA, (Note 2)	$V_{BR2}$	13.5	15	15.8	V
Reverse Leakage Current ( $D_1, D_2, D_3,$ and $D_4$ )	@ $V_{RWM1}$	$I_R$	-	-	1.0	$\mu\text{A}$
Reverse Leakage Current ( $V_1, V_2$ )	@ $V_{RWM2}$	$I_R$	-	-	1.0	$\mu\text{A}$
Capacitance ( $D_1, D_2, D_3,$ and $D_4$ )	$V_R = 0$ V, $f = 1$ MHz (Line to GND)	$C_J$	-	0.7	0.9	pF
Clamping Voltage	@ $I_{PP} = 1$ A (Note 3)	$V_C$	-	-	14.3	V
Clamping Voltage	Per IEC61000-4-2 (Note 4)	$V_C$	Figures 1 and 2			V

1. Surge protection devices are normally selected according to the working peak reverse voltage ( $V_{RWM}$ ), which should be equal or greater than the DC or continuous peak operating voltage level.
2.  $V_{BR}$  is measured at pulse test current  $I_T$ .
3. Surge current waveform per Figure 5.
4. Typical waveform. For test procedure see Figures 3 and 4 and Application Note AND8307/D.

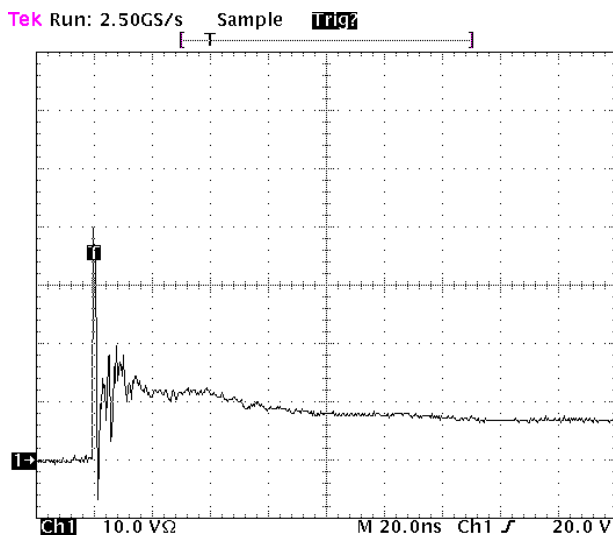


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

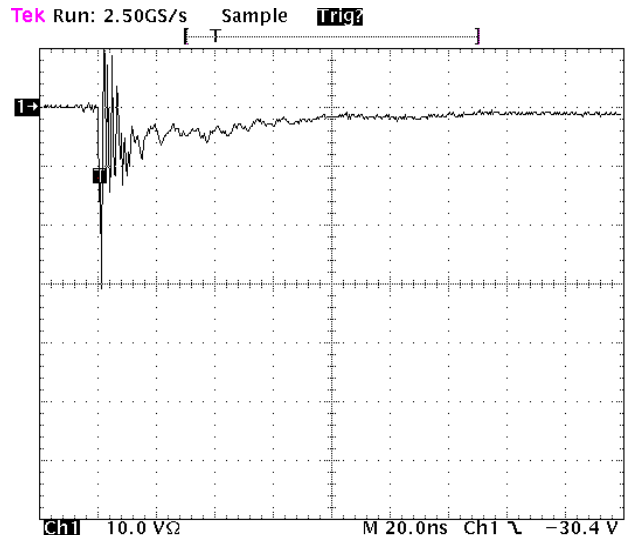


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

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## IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

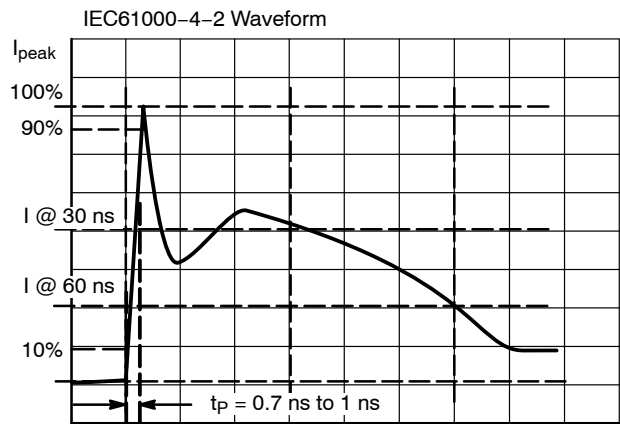


Figure 3. IEC61000-4-2 Spec

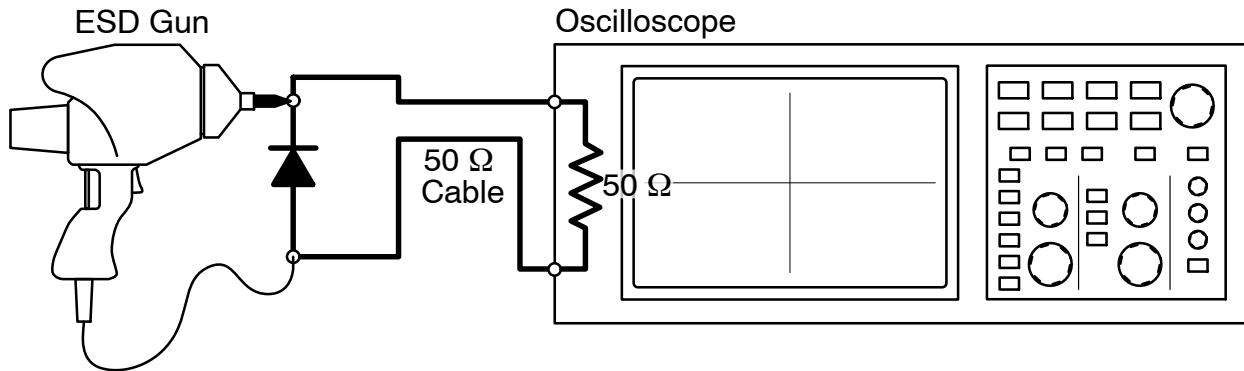


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

### ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

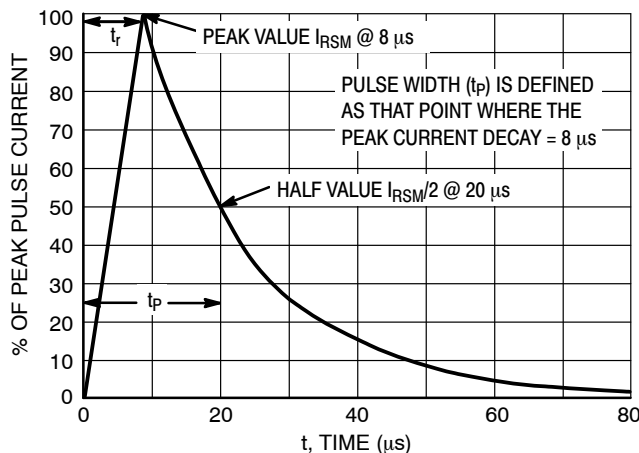
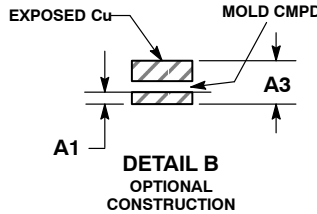
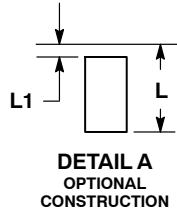
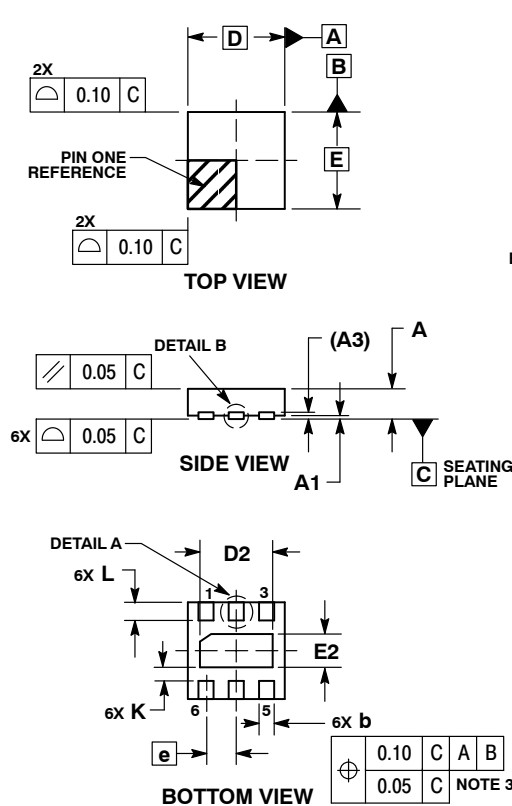


Figure 5. 8 X 20 μs Pulse Waveform

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## PACKAGE DIMENSIONS

UDFN6, 1.6x1.6, 0.5P  
CASE 517AP-01  
ISSUE O

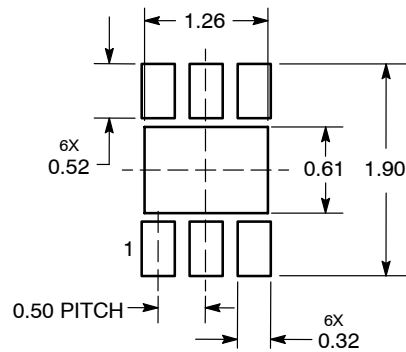


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.20	0.30
D	1.60 BSC	
E	1.60 BSC	
e	0.50 BSC	
D2	1.10	1.30
E2	0.45	0.65
K	0.20	---
L	0.20	0.40
L1	0.00	0.15

### SOLDERMASK DEFINED MOUNTING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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